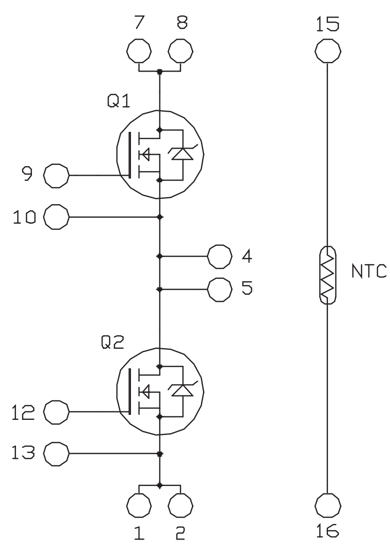
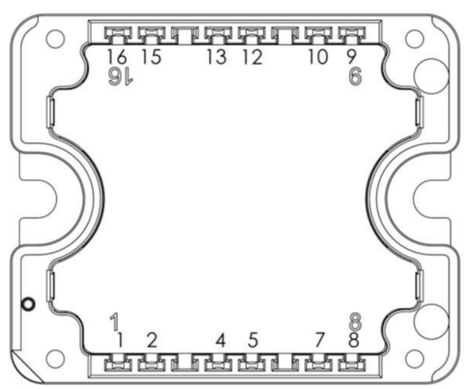
MSCSM120AM16T1AG

Phase Leg SiC MOSFET Power Module

Product Overview

The MSCSM120AM16T1AG device is a phase leg 1200V, 173A silicon carbide (SiC) MOSFET power module.





Notes:

- Pins 1/2; 4/5; 7/8 must be shorted together.
- All ratings at T_J = 25 °C, unless otherwise specified.

⚠ CAUTION These devices are sensitive to electrostatic discharge. Proper handling procedures must be followed.

Features

The following are key features of the MSCSM120AM16T1AG device:

- SiC Power MOSFET
  - Low $R_{DS(on)}$
  - High temperature performance
- Very low stray inductance
- Kelvin source for an easy drive
- Internal thermistor for temperature monitoring
- Aluminum Nitride (AlN) substrate for improved thermal performance

Benefits

The following are the benefits of MSCSM120AM16T1AG device:

- High power and efficiency converters and inverters
- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction-to-case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS compliant

Application

The MSCSM120AM16T1AG device is designed for the following applications:

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- EV motor and traction drive

1. Electrical Specifications

This section provides the electrical specifications of the MSCSM120AM16T1AG device.

1.1 SiC MOSFET Characteristics (Per SiC MOSFET)

The following table lists the absolute maximum ratings per SiC MOSFET of the MSCSM120AM16T1AG device.

Table 1-1. Absolute Maximum Ratings

Symbol	Parameter		Maximum Ratings	Unit
V_{DSS}	Drain-Source voltage		1200	V
I_D	Continuous drain current	T_C = 25 °C	173[1]	A
		T_C = 80 °C	138[1]	
I_{DM}	Pulsed drain current		350	
V_{GS}	Gate-Source voltage		–10/23	V
$R_{DS(on)}$	Drain-Source ON resistance		16	mΩ
P_D	Power dissipation	T_C = 25 °C	745	W

Note:

1. SiC MOSFET device specification, but the output current must be limited due to the size of the power connectors.

The following table lists the electrical characteristics per SiC MOSFET of the MSCSM120AM16T1AG device.

Table 1-2. Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
I_{DSS}	Zero gate voltage drain current	V_{GS} = 0V V_{DS} = 1200V		—	20	200	µA
$R_{DS(on)}$	Drain–Source on resistance	V_{GS} = 20V	T_J = 25 °C	—	12.5	16	mΩ
		I_D = 80A	T_J = 175 °C	—	20	—	
$V_{GS(th)}$	Gate threshold voltage	V_{GS} = V_{DS} I_D = 6 mA		1.8	2.8	—	V
I_{GSS}	Gate–Source leakage current	V_{GS} = 20V; V_{DS} = 0V		—	—	200	nA

The following table lists the dynamic characteristics per SiC MOSFET of the MSCSM120AM16T1AG device.

Table 1-3. Dynamic Characteristics

Symbol	Characteristic	Test Conditions		Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	V_{GS} = 0V V_{DS} = 1000V f = 1 MHz		—	6040	—	pF
C_{oss}	Output capacitance			—	540	—	
C_{rss}	Reverse transfer capacitance			—	50	—	
Q_g	Total gate charge	V_{GS} = –5V/20V V_{Bus} = 800V I_D = 80A		—	464	—	nC
Q_{gs}	Gate-Source charge			—	82	—	
Q_{gd}	Gate-Drain charge			—	100	—	
$T_{d(on)}$	Turn-on delay time	V_{GS} = –5V/20V V_{Bus} = 600V I_D = 100A $R_{G(on)}$ = 4Ω $R_{G(off)}$ = 2.4Ω		—	30	—	ns
T_r	Rise time			—	30	—	
$T_{d(off)}$	Turn-off delay time			—	50	—	
T_f	Fall time				25	—	
E_{on}	Turn-on energy	V_{GS} = –5V/20V V_{Bus} = 600V I_D = 100A $R_{G(on)}$ = 4Ω $R_{G(off)}$ = 2.4Ω	T_J = 150 °C	—	2.4	—	mJ
E_{off}	Turn-off energy			—	1.3	—	
R_{Gint}	Internal gate resistance			—	2.94	—	Ω
R_{thJC}	Junction-to-case thermal resistance			—	—	0.2	°C/W

The following table lists the body diode ratings and characteristics per SiC MOSFET of the MSCSM120AM16T1AG device.

Table 1-4. Body Diode Ratings and Characteristics

Symbol	Characteristic	Test Conditions	Min.	Typ.	Max.	Unit
V_{SD}	Diode forward voltage	V_{GS} = 0V; I_{SD} = 80A	—	4	—	V
		V_{GS} = –5V; I_{SD} = 80A	—	4.2	—	
t_{rr}	Reverse recovery time	I_{SD} = 80A; V_{GS} = –5V V_R = 800V; di_F/dt = 2000 A/µs	—	90	—	ns
Q_{rr}	Reverse recovery charge		—	1100	—	nC
I_{rr}	Reverse recovery current		—	27	—	A

1.2 Thermal and Package Characteristics

The following table lists the thermal and package characteristics of the MSCSM120AM16T1AG device.

Table 1-5. Thermal and Package Characteristics

Symbol	Characteristics			Min.	Max.	Unit
V_{ISOL}	RMS isolation voltage, any terminal to case t =1 min, 50 Hz/60 Hz			4000	—	V
T_J	Operating junction temperature range			–40	175	°C
T_{JOP}	Recommended junction temperature under switching conditions			–40	T_{Jmax}–25	
T_{STG}	Storage temperature range			–40	125	
T_C	Operating case temperature			–40	125	
Torque	Mounting torque	To heatsink	M4	2	3	N.m
Wt	Package weight			—	80	g

The following table lists the temperature sensor NTC of the MSCSM120AM16T1AG device.

Table 1-6. Temperature Sensor NTC

Symbol	Characteristic		Min.	Typ.	Max.	Unit
R_{25}	Resistance at 25 °C		—	50	—	kΩ
$\Delta R_{25}/R_{25}$	—	—	—	5	—	%
$B_{25/85}$	T_{25} = 298.15K	—	—	3952	—	K
ΔB/B	—	T_C = 100 °C	—	4	—	%

$$R_T = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$$

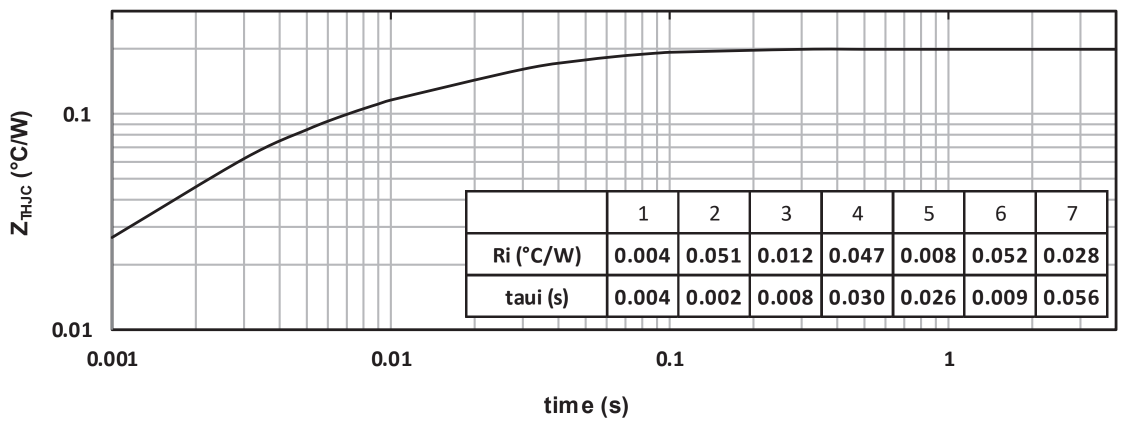
T: Thermistor temperature
R_T: Thermistor value at T

Note: See APT0406—Using NTC Temperature Sensor Integrated into Power Module for more information.

1.3 Typical SiC MOSFET Performance Curve

This section shows the typical SiC MOSFET performance curves of the MSCSM120AM16T1AG device.

Figure 1-1. Maximum Thermal Impedance



	1	2	3	4	5	6	7
Ri (°C/W)	0.004	0.051	0.012	0.047	0.008	0.052	0.028
taui (s)	0.004	0.002	0.008	0.030	0.026	0.009	0.056

Figure 1-2. Output Characteristics, T_J = 25 °C

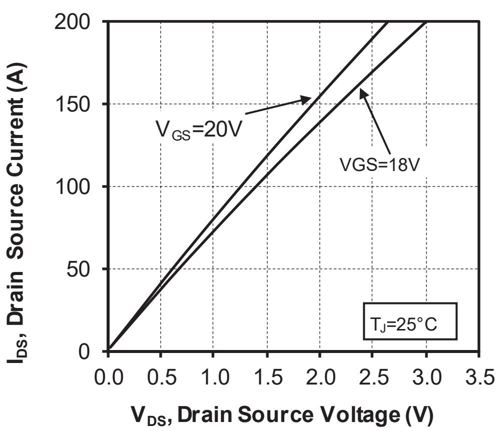


Figure 1-3. Output Characteristics, T_J = 175 °C

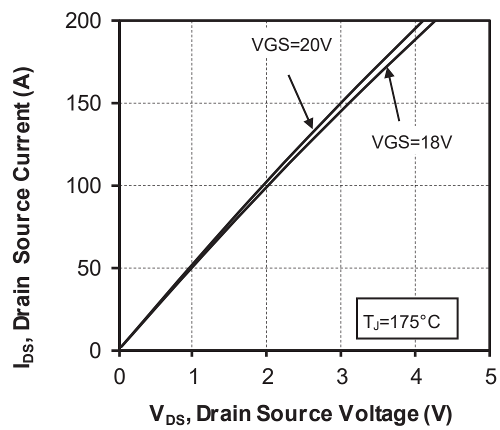


Figure 1-4. Normalized $R_{DS(on)}$ vs. Temperature

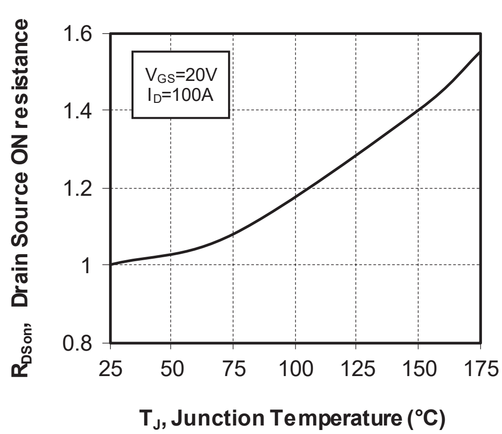


Figure 1-5. Transfer Characteristics

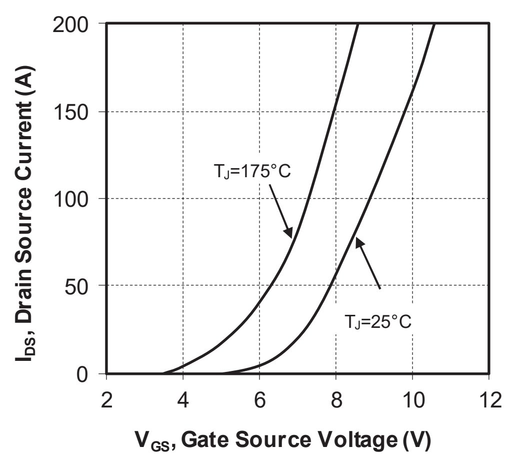


Figure 1-6. Switching Energy vs. Current

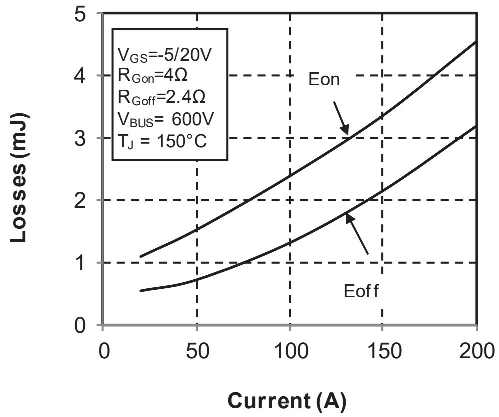


Figure 1-7. Switching Energy vs. Rg

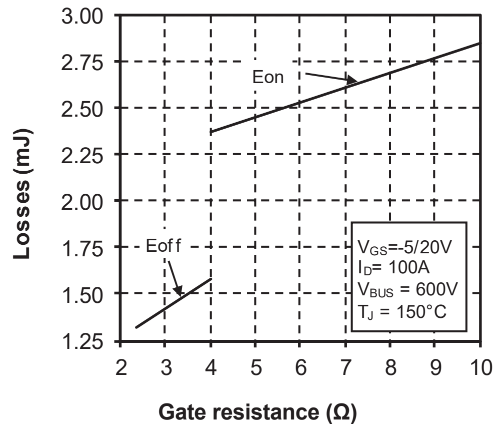


Figure 1-8. Capacitance vs. Drain Source Voltage

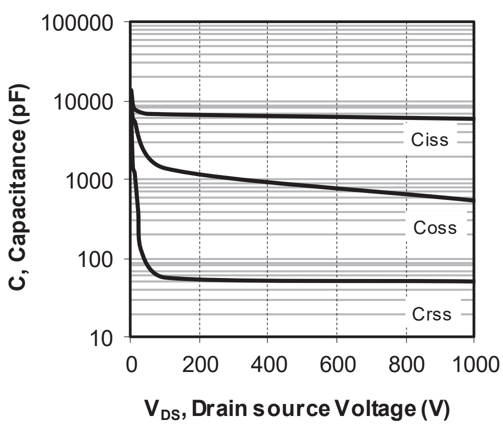


Figure 1-9. Gate Charge vs. Gate Source Voltage

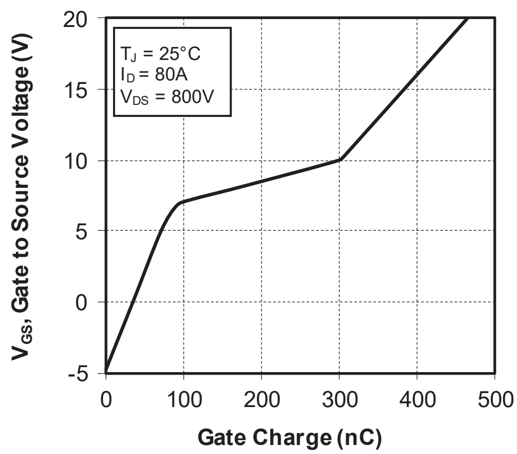


Figure 1-10. Body Diode Characteristics, T_J = 25 °C

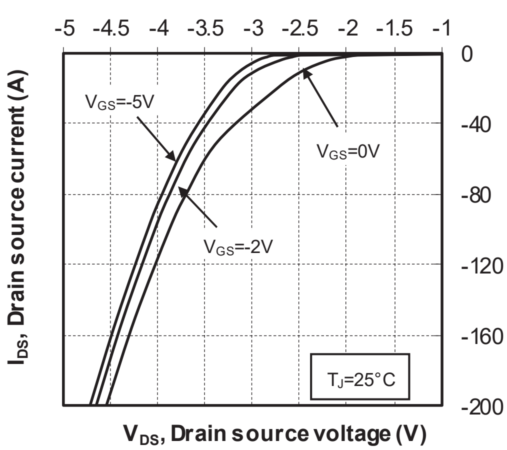


Figure 1-11. 3rd Quadrant Characteristics, T_J = 25 °C

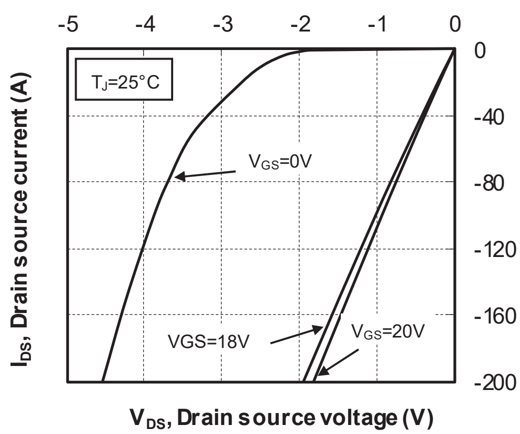


Figure 1-12. Body Diode Characteristics, T_J = 175 °C

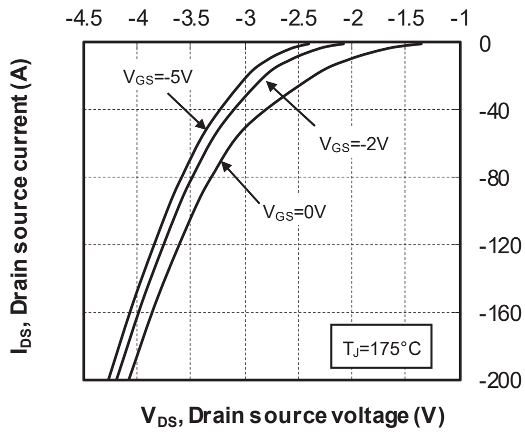


Figure 1-13. 3rd Quadrant Characteristics, T_J = 175 °C

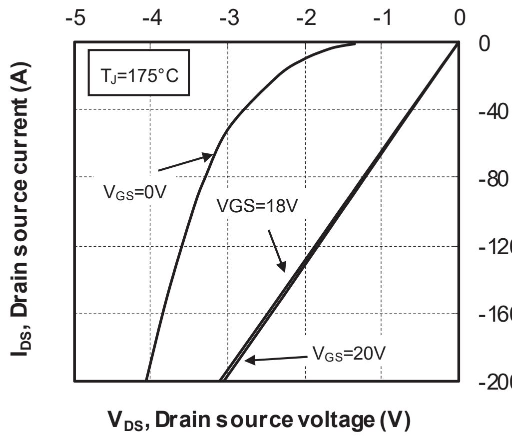
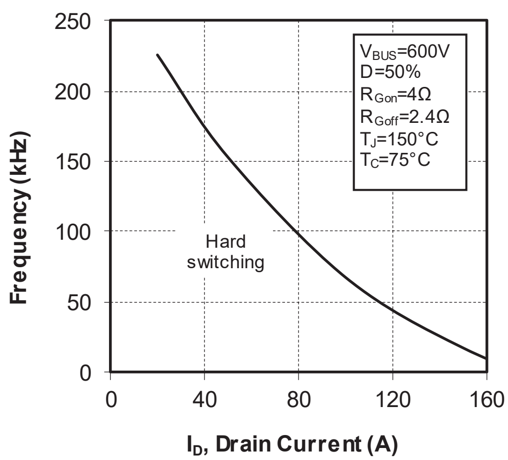


Figure 1-14. Operating Frequency vs Drain Current



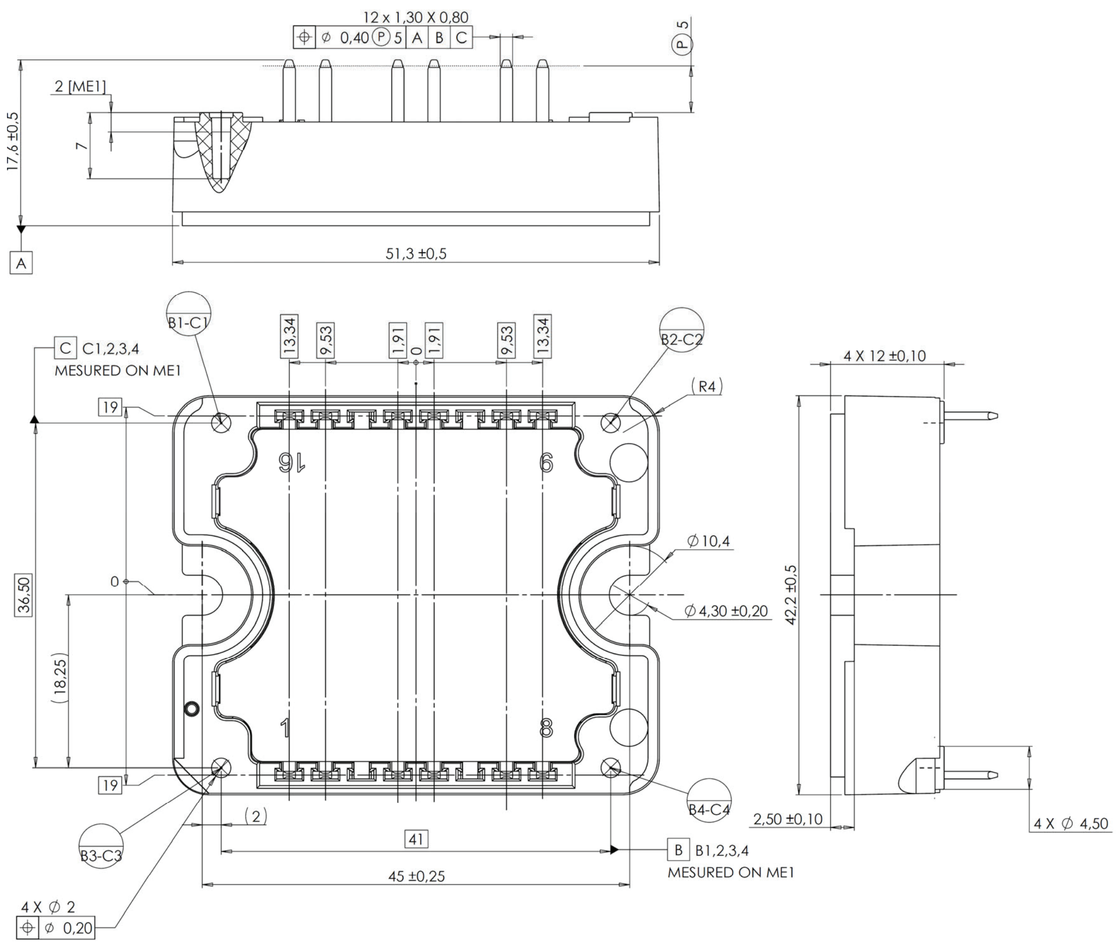
2. Package Specifications

The following section shows the package specification of the MSCSM120AM16T1AG device.

2.1 Package Outline

The following figure shows the package outline drawing of the MSCSM120AM16T1AG device. The dimensions in the following figure are in millimeters.

Figure 2-1. Package Outline Drawing



Note: See AN3500A - Mounting instructions for SP1F and SP3F Power Modules for more information.

3. Revision History

Revision	Date	Description
A	06/2022	Initial Revision

Microchip Information

The Microchip Website

Microchip provides online support via our website at www.microchip.com/. This website is used to make files and information easily available to customers. Some of the content available includes:

- **Product Support** – Data sheets and errata, application notes and sample programs, design resources, user's guides and hardware support documents, latest software releases and archived software
- **General Technical Support** – Frequently Asked Questions (FAQs), technical support requests, online discussion groups, Microchip design partner program member listing
- **Business of Microchip** – Product selector and ordering guides, latest Microchip press releases, listing of seminars and events, listings of Microchip sales offices, distributors and factory representatives

Product Change Notification Service

Microchip's product change notification service helps keep customers current on Microchip products. Subscribers will receive email notification whenever there are changes, updates, revisions or errata related to a specified product family or development tool of interest.

To register, go to www.microchip.com/pcn and follow the registration instructions.

Customer Support

Users of Microchip products can receive assistance through several channels:

- Distributor or Representative
- Local Sales Office
- Embedded Solutions Engineer (ESE)
- Technical Support

Customers should contact their distributor, representative or ESE for support. Local sales offices are also available to help customers. A listing of sales offices and locations is included in this document.

Technical support is available through the website at: www.microchip.com/support

Microchip Devices Code Protection Feature

Note the following details of the code protection feature on Microchip products:

- Microchip products meet the specifications contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is secure when used in the intended manner, within operating specifications, and under normal conditions.
- Microchip values and aggressively protects its intellectual property rights. Attempts to breach the code protection features of Microchip product is strictly prohibited and may violate the Digital Millennium Copyright Act.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of its code. Code protection does not mean that we are guaranteeing the product is "unbreakable". Code protection is constantly evolving. Microchip is committed to continuously improving the code protection features of our products.

Legal Notice

This publication and the information herein may be used only with Microchip products, including to design, test, and integrate Microchip products with your application. Use of this information in any other manner violates these terms. Information regarding device applications is provided only for your convenience and may be superseded

Trademarks

ISBN: 978-1-6683-0711-3

Quality Management System

For information regarding Microchip's Quality Management Systems, please visit www.microchip.com/quality.

Worldwide Sales and Service

AMERICAS	ASIA/PACIFIC	ASIA/PACIFIC	EUROPE
Corporate Office 2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support: www.microchip.com/support Web Address: www.microchip.com **Atlanta** Duluth, GA Tel: 678-957-9614 Fax: 678-957-1455 **Austin, TX** Tel: 512-257-3370 **Boston** Westborough, MA Tel: 774-760-0087 Fax: 774-760-0088 **Chicago** Itasca, IL Tel: 630-285-0071 Fax: 630-285-0075 **Dallas** Addison, TX Tel: 972-818-7423 Fax: 972-818-2924 **Detroit** Novi, MI Tel: 248-848-4000 **Houston, TX** Tel: 281-894-5983 **Indianapolis** Noblesville, IN Tel: 317-773-8323 Fax: 317-773-5453 Tel: 317-536-2380 **Los Angeles** Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608 Tel: 951-273-7800 **Raleigh, NC** Tel: 919-844-7510 **New York, NY** Tel: 631-435-6000 **San Jose, CA** Tel: 408-735-9110 Tel: 408-436-4270 **Canada - Toronto** Tel: 905-695-1980 Fax: 905-695-2078	**Australia - Sydney** Tel: 61-2-9868-6733 **China - Beijing** Tel: 86-10-8569-7000 **China - Chengdu** Tel: 86-28-8665-5511 **China - Chongqing** Tel: 86-23-8980-9588 **China - Dongguan** Tel: 86-769-8702-9880 **China - Guangzhou** Tel: 86-20-8755-8029 **China - Hangzhou** Tel: 86-571-8792-8115 **China - Hong Kong SAR** Tel: 852-2943-5100 **China - Nanjing** Tel: 86-25-8473-2460 **China - Qingdao** Tel: 86-532-8502-7355 **China - Shanghai** Tel: 86-21-3326-8000 **China - Shenyang** Tel: 86-24-2334-2829 **China - Shenzhen** Tel: 86-755-8864-2200 **China - Suzhou** Tel: 86-186-6233-1526 **China - Wuhan** Tel: 86-27-5980-5300 **China - Xian** Tel: 86-29-8833-7252 **China - Xiamen** Tel: 86-592-2388138 **China - Zhuhai** Tel: 86-756-3210040	**India - Bangalore** Tel: 91-80-3090-4444 **India - New Delhi** Tel: 91-11-4160-8631 **India - Pune** Tel: 91-20-4121-0141 **Japan - Osaka** Tel: 81-6-6152-7160 **Japan - Tokyo** Tel: 81-3-6880- 3770 **Korea - Daegu** Tel: 82-53-744-4301 **Korea - Seoul** Tel: 82-2-554-7200 **Malaysia - Kuala Lumpur** Tel: 60-3-7651-7906 **Malaysia - Penang** Tel: 60-4-227-8870 **Philippines - Manila** Tel: 63-2-634-9065 **Singapore** Tel: 65-6334-8870 **Taiwan - Hsin Chu** Tel: 886-3-577-8366 **Taiwan - Kaohsiung** Tel: 886-7-213-7830 **Taiwan - Taipei** Tel: 886-2-2508-8600 **Thailand - Bangkok** Tel: 66-2-694-1351 **Vietnam - Ho Chi Minh** Tel: 84-28-5448-2100	**Austria - Wels** Tel: 43-7242-2244-39 Fax: 43-7242-2244-393 **Denmark - Copenhagen** Tel: 45-4485-5910 Fax: 45-4485-2829 **Finland - Espoo** Tel: 358-9-4520-820 **France - Paris** Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79 **Germany - Garching** Tel: 49-8931-9700 **Germany - Haan** Tel: 49-2129-3766400 **Germany - Heilbronn** Tel: 49-7131-72400 **Germany - Karlsruhe** Tel: 49-721-625370 **Germany - Munich** Tel: 49-89-627-144-0 Fax: 49-89-627-144-44 **Germany - Rosenheim** Tel: 49-8031-354-560 **Israel - Ra'anana** Tel: 972-9-744-7705 **Italy - Milan** Tel: 39-0331-742611 Fax: 39-0331-466781 **Italy - Padova** Tel: 39-049-7625286 **Netherlands - Drunen** Tel: 31-416-690399 Fax: 31-416-690340 **Norway - Trondheim** Tel: 47-72884388 **Poland - Warsaw** Tel: 48-22-3325737 **Romania - Bucharest** Tel: 40-21-407-87-50 **Spain - Madrid** Tel: 34-91-708-08-90 Fax: 34-91-708-08-91 **Sweden - Gothenberg** Tel: 46-31-704-60-40 **Sweden - Stockholm** Tel: 46-8-5090-4654 **UK - Wokingham** Tel: 44-118-921-5800 Fax: 44-118-921-5820